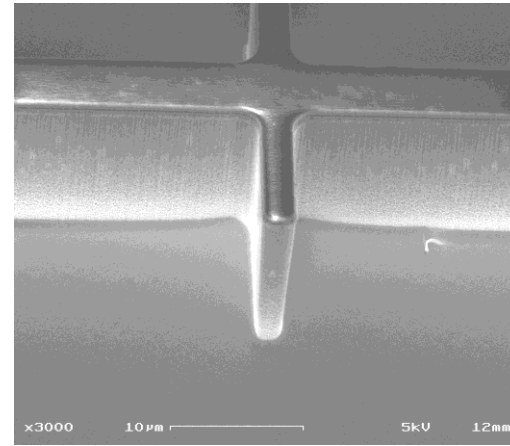
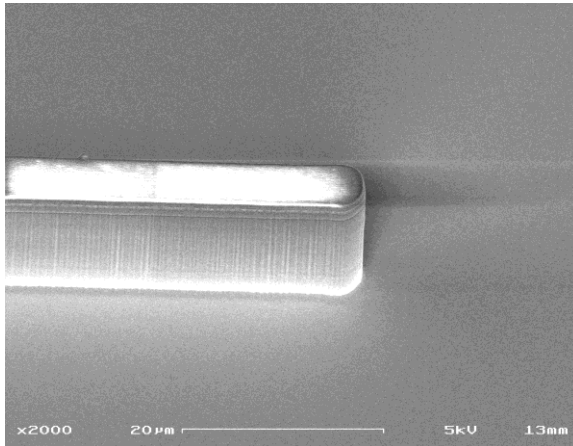


# InP Ridges

**Substrate:** InP  
**Chemistry:** HBr, N<sub>2</sub>  
**Mask:** SU8  
**Selectivity:** > 10:1  
**Etch rate:** ~ 2.0 um/min

**HBr flow:** 60 sccm  
**N<sub>2</sub> flow:** 9 sccm  
**Pressure:** 5 mTorr  
**ICP power:** 600 W  
**RF bias:** 100 W  
**Temperature:** 180°C



**clean & smooth etch surface, 10 – 15 um deep etch, vertical side wall, greater than 10:1 selectivity to SU-8**